

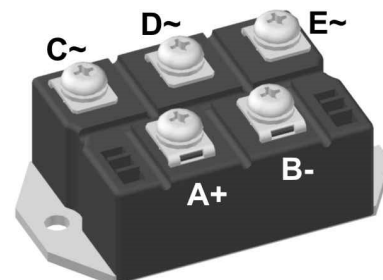
Standard Rectifier Module

3~ Rectifier	
V_{RRM}	= 1200 V
I_{DAV}	= 240 A
I_{FSM}	= 2800 A

3~ Rectifier Bridge

Part number

VUO190-12NO7



 E72873



Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

- Diode for main rectification
- For three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Package: PWS-E

- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Easy to mount with two screws
- Base plate: Copper internally DCB isolated
- Advanced power cycling

Disclaimer Notice

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Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1300	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1200	V
I_R	reverse current	$V_R = 1200\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			200	μA
		$V_R = 1200\text{ V}$	$T_{VJ} = 150^{\circ}\text{C}$			3.5	mA
V_F	forward voltage drop	$I_F = 80\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			1.07	V
		$I_F = 240\text{ A}$				1.36	V
		$I_F = 80\text{ A}$	$T_{VJ} = 125^{\circ}\text{C}$			0.96	V
		$I_F = 240\text{ A}$				1.33	V
I_{DAV}	bridge output current	$T_C = 110^{\circ}\text{C}$ rectangular $d = \frac{1}{3}$	$T_{VJ} = 150^{\circ}\text{C}$			240	A
V_{F0}	threshold voltage	} for power loss calculation only	$T_{VJ} = 150^{\circ}\text{C}$			0.74	V
r_F	slope resistance					2.4	m Ω
R_{thJC}	thermal resistance junction to case					0.4	K/W
R_{thCH}	thermal resistance case to heatsink				0.15		K/W
P_{tot}	total power dissipation		$T_C = 25^{\circ}\text{C}$			310	W
I_{FSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			2.80	kA
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			3.03	kA
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}\text{C}$			2.38	kA
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			2.57	kA
I^2t	value for fusing	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			39.2	kA ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			38.1	kA ² s
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}\text{C}$			28.3	kA ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			27.5	kA ² s
C_J	junction capacitance	$V_R = 400\text{ V}; f = 1\text{ MHz}$	$T_{VJ} = 25^{\circ}\text{C}$		133		pF

Package PWS-E				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
I_{RMS}	RMS current	per terminal			250	A	
T_{VJ}	virtual junction temperature		-40		150	°C	
T_{op}	operation temperature		-40		125	°C	
T_{stg}	storage temperature		-40		125	°C	
Weight					284	g	
M_D	mounting torque		4.25		5.75	Nm	
M_T	terminal torque		4.25		5.75	Nm	
$d_{Spp/Apb}$	creepage distance on surface striking distance through air	terminal to terminal	12.0			mm	
$d_{Spb/Apb}$		terminal to backside	26.0			mm	
V_{ISOL}	isolation voltage	t = 1 second	3000			V	
		t = 1 minute	2500			V	



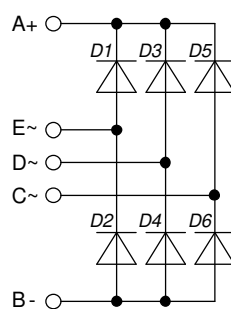
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VUO190-12NO7	VUO190-12NO7	Box	5	462497

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 150^{\circ}\text{C}$

		Rectifier	
$V_{0\max}$	threshold voltage	0.74	V
$R_{0\max}$	slope resistance *	1.2	mΩ



Rectifier


Fig. 1 Forward current vs. voltage drop per diode



Fig. 2 Surge overload current vs. time per diode

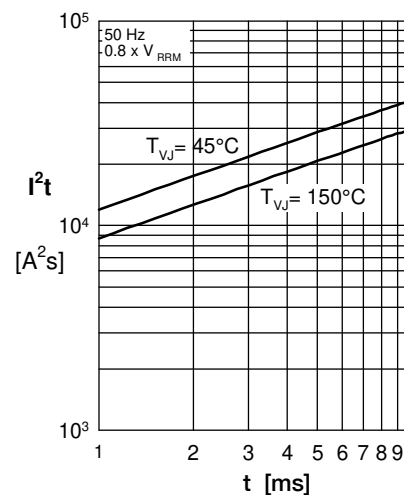
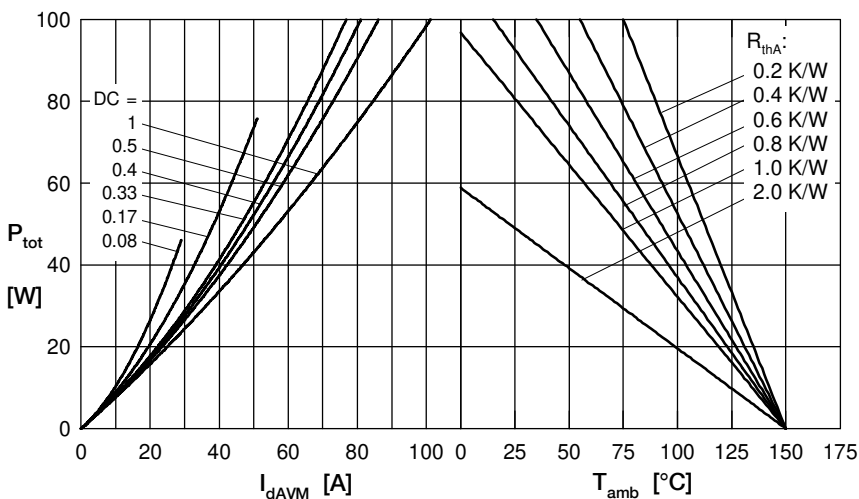

 Fig. 3 I^2t vs. time per diode


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

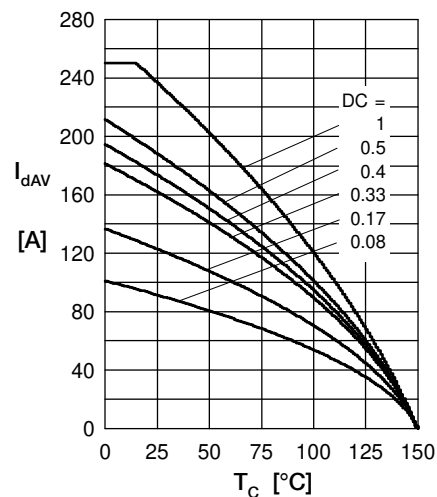


Fig. 5 Max. forward current vs. case temperature per diode

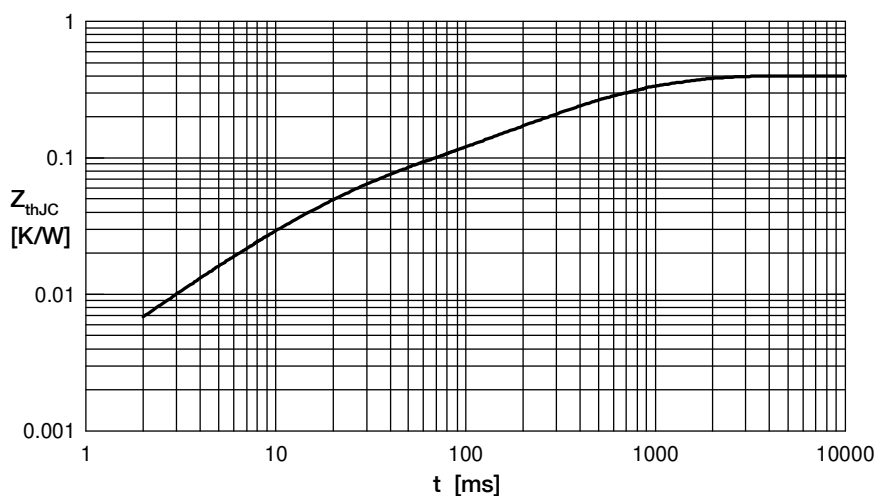


Fig. 6 Transient thermal impedance junction to case vs. time per diode

R_i	t_i
0.050	0.02
0.003	0.01
0.100	0.225
0.177	0.8
0.070	0.58